

BC860

Rev.F Apr.-2017

VRW056 塑料封装 SOT-23 硅 PNP 晶体管 Silicon PNP transistor in a SOT-23 Plastic Package.

高电流增益，低集电极-发射极饱和电压 $V_{CE(sat)}$

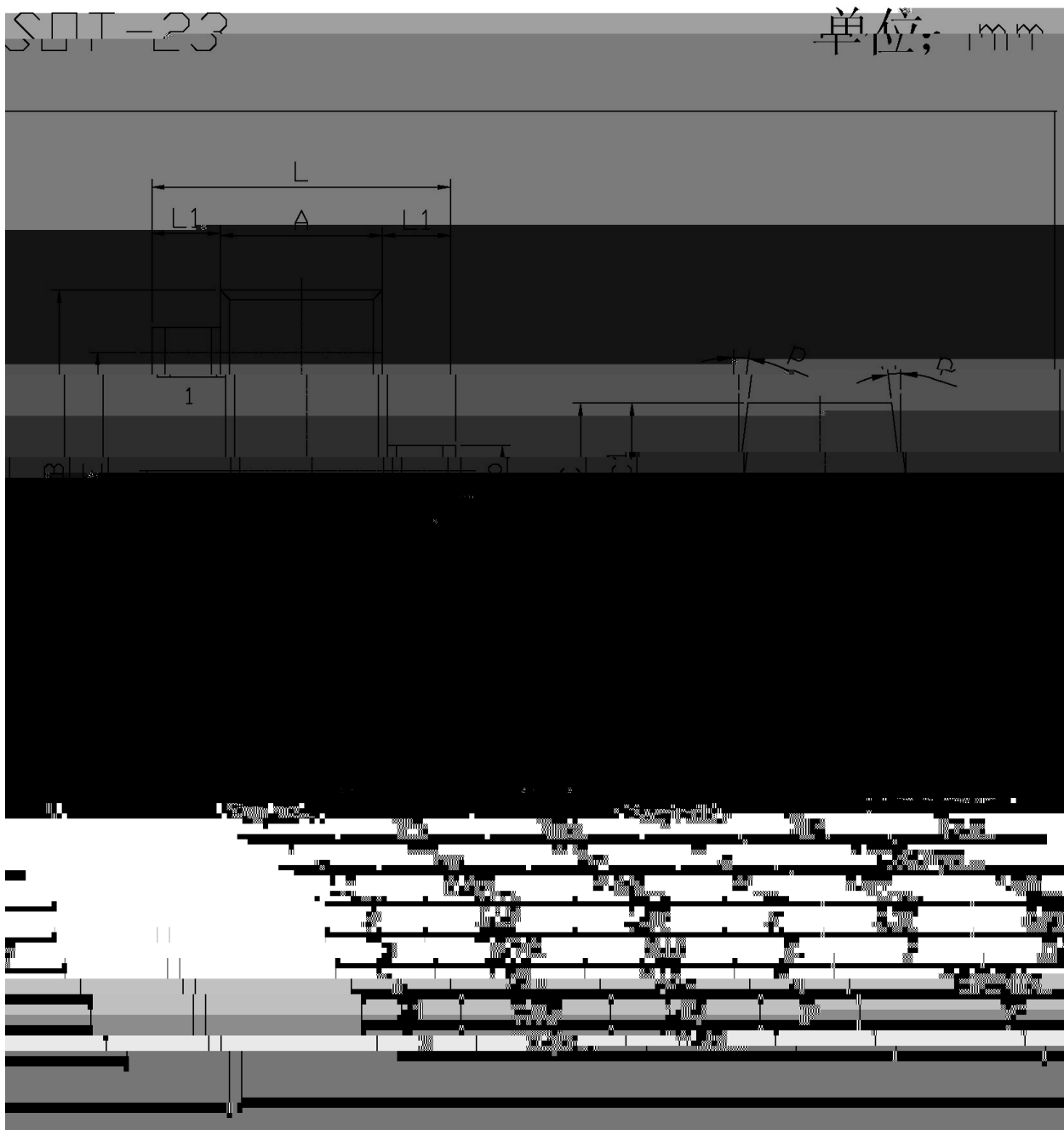
High current gain, Low collector-emitter saturation voltage.

典型值 $f_{T(0.1)}$

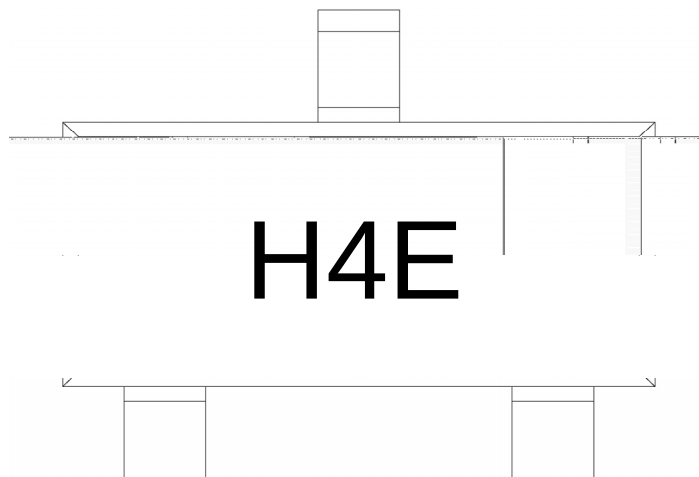
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-50	V
Collector to Emitter Voltage	V_{CEO}	-45	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-100	mA
Collector Power Dissipation	P_C	350	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 ~ 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C = -10mA$ $I_B = 0$	-45			V
Collector to Base Breakdown Voltage	V_{CBO}	$I_C = I_E$				

/ Package Dimensions



/ Marking Instructions



б " X

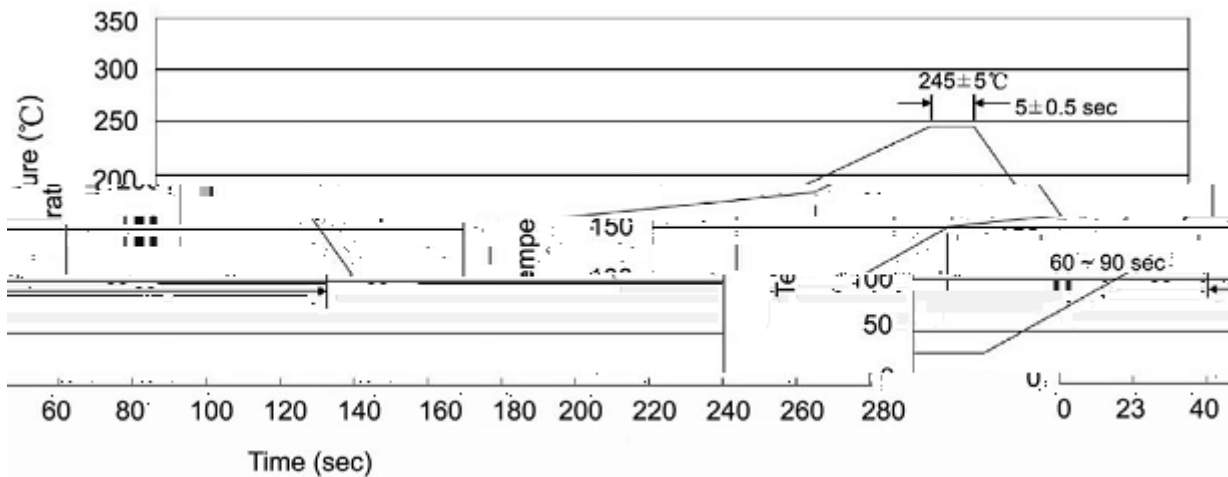
K X № 3¹ П

7H X № 3^N П

Note:

H: Company Code.

4E: Product Type Code


() / Temperature Profile for IR Reflow Soldering(Pb-Free)


℃ ×

1. 预加热: 25~150℃, 时间: 60~90sec;
2. 峰值温度: 245±5℃, 持续时间: 5±0.5sec;
3. 冷却速度: 2~10℃/sec.

Note:

1. Preheating: 25~150℃, Time: 60~90sec.
2. Peak Temp.: 245±5℃, Duration: 5±0.5sec.
3. Cooling Speed: 2~10℃/sec.

/ Resistance to Soldering Heat Test Conditions

□ 温度: 260±5

时间: 10±1 sec.

Temp.: 260±5

Time: 10±1 sec

/ Packaging SPEC.

包装形式 / REEL

Package Type	Units					Dimension (unit: mm ³)		

/ Notices